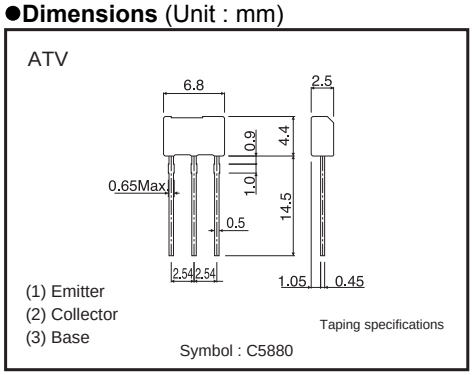
Power transistor (60V, 2A)

2SC5880

●Features

1) High speed switching.
   (tf : Typ. : 35ns at I_C = 2A)
2) Low saturation voltage, typically
   (Typ. : 200mV at I_C = 1.0A, I_B = 100mA)
3) Strong discharge power for inductive load and capacitance load.
4) Complements the 2SA2093

●Dimensions (Unit : mm)



●Applications

Low frequency amplifier
High speed switching

●Structure

NPN Silicon epitaxial planar transistor

●Packaging specifications

Type	Package	Taping
	Code	TV2
	Basic ordering unit (pieces)	2500
2SC5880		◯

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Collector-base voltage		V_{CBO}	60	V
Collector-emitter voltage		V_{CEO}	60	V
Emitter-base voltage		V_{EBO}	6	V
Collector current	DC	I_C	2	A
	Pulsed	I_{CP}	4	A *
Power dissipation		P_C	1.0	W
Junction temperature		t_j	150	°C
Range of storage temperature		t_{stg}	−55 to 150	°C

*Pw=10ms

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Collector-emitter breakdown voltage	BV_{CEO}	60	–	–	V	I_C=1mA
Collector-base breakdown voltage	BV_{CBO}	60	–	–	V	I_C=100μA
Emitter-base breakdown voltage	BV_{EBO}	6	–	–	V	I_E=100μA
Collector cut-off current	I_{CBO}	–	–	1.0	μA	V_{CB}=40V
Emitter cut-off current	I_{EBO}	–	–	1.0	μA	V_{EB}=4V
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	–	200	500	mV	I_C=1.0A I_B=0.1A
DC current gain	h_{FE}	120	–	390	–	V_{CE}=2V I_C=100mA
Transition frequency	f_T	–	200	–	MHz	V_{CE}=10V * I_E= −100mA f=10MHz
Corrector output capacitance	Cob	–	10	–	pF	V_{CB}=10V I_E=0mA f=1MHz
Turn-on time	t_{on}	–	50	–	ns	I_C=2A I_{B1}=200mA I_{B2}= −200mA V_{CC}≒25V
Storage time	t_{stg}	–	120	–	ns	
Fall time	t_f	–	35	–	ns	

*Non repetitive pulse

●h_{FE} RANK

Q	R
120–270	180–390

●Electrical characteristic curves

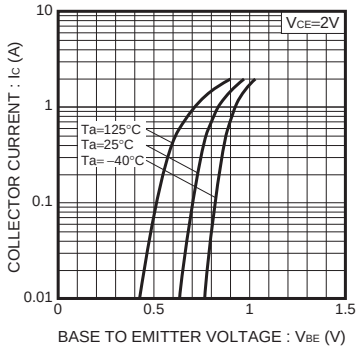


Fig.1 Grounded Emitter Propagation Characteristics

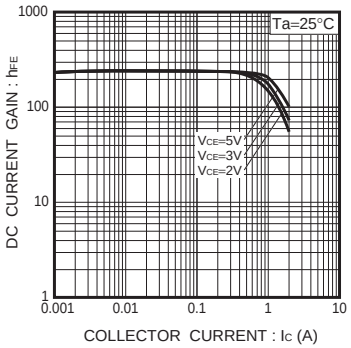


Fig.2 DC Current Gain vs. Collector Current (I)

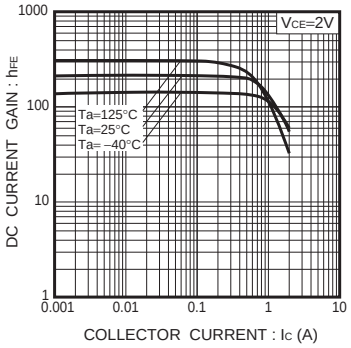


Fig.3 DC Current Gain vs. Collector Current (II)

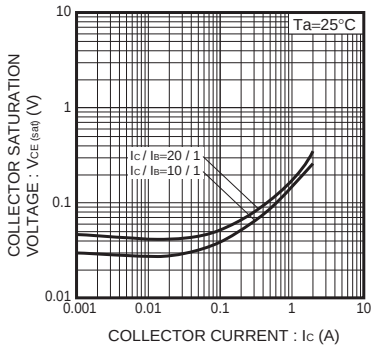


Fig.4 Collector-Emitter Saturation Voltage vs. Collector Current (I)

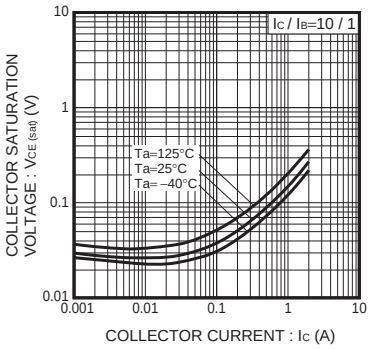


Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (II)

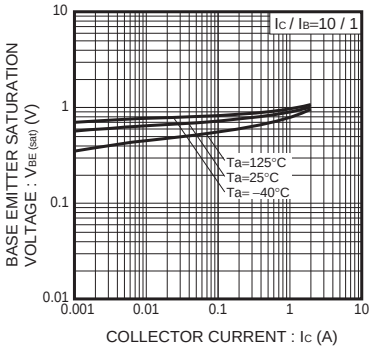


Fig.6 Base-Emitter Saturation Voltage vs. Collecter Current

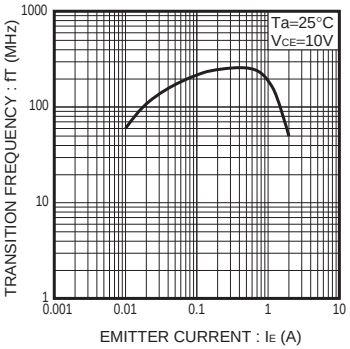


Fig.7 Transition Frequency

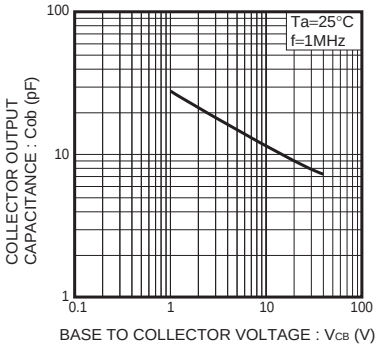


Fig.8 Collector Output Capacitance

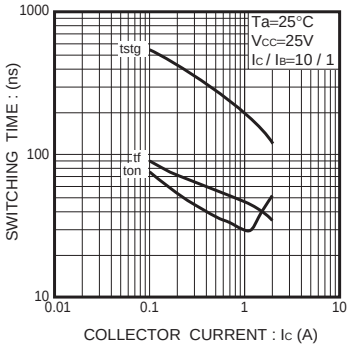
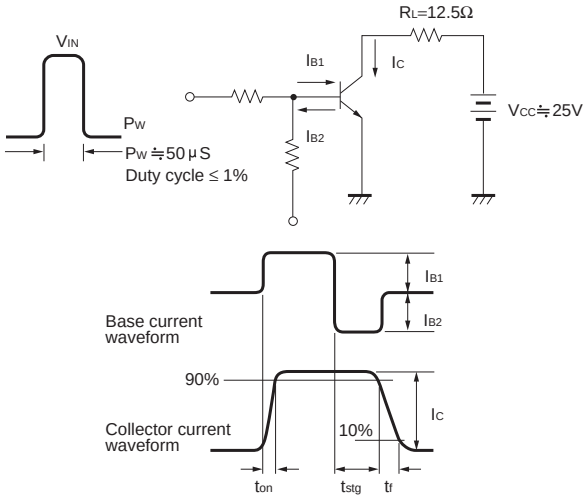


Fig.9 Switching Time

●Switching characteristics measurement circuits



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